

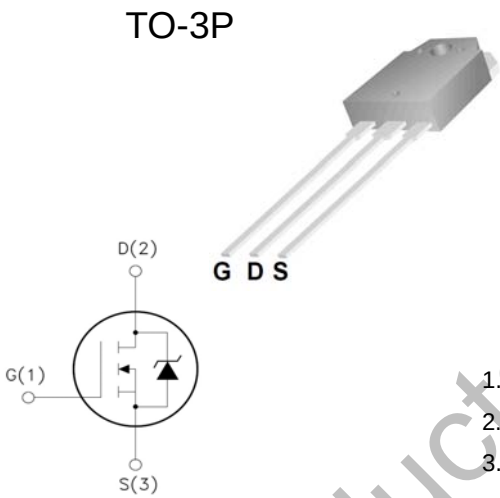


WGE13009L

Features:

- ☐ High Voltage Capability
- ☐ High Switching Speed
- ☐ Suitable for Electronic Ballast and Switching Mode Power Supply
- ☐ 100% Avalanche Tested

TO-3P



1. Gate (G)
2. Drain (D)
3. Source (S)



Absolute Maximum Ratings*T_C = 25°C unless otherwise noted

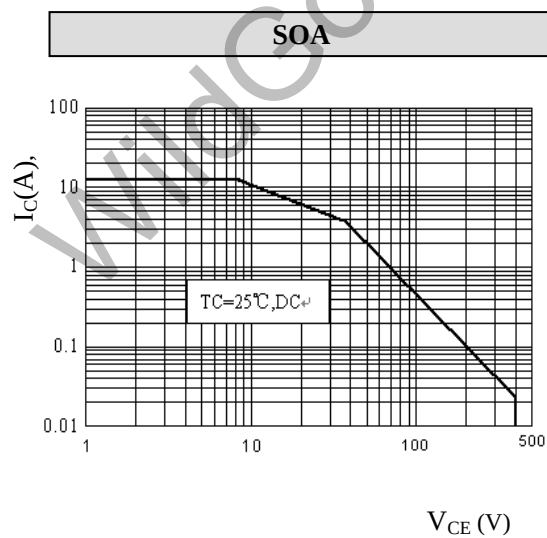
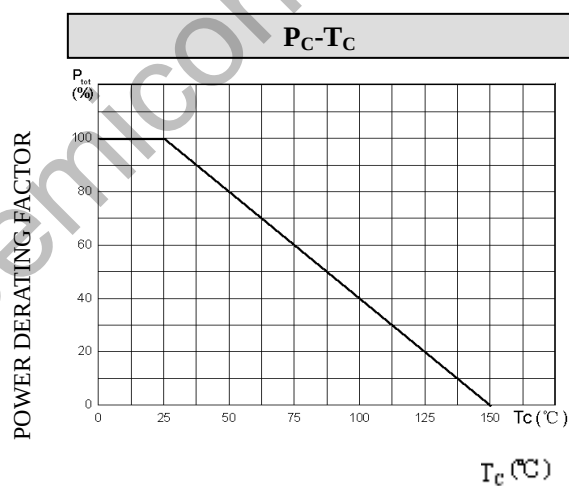
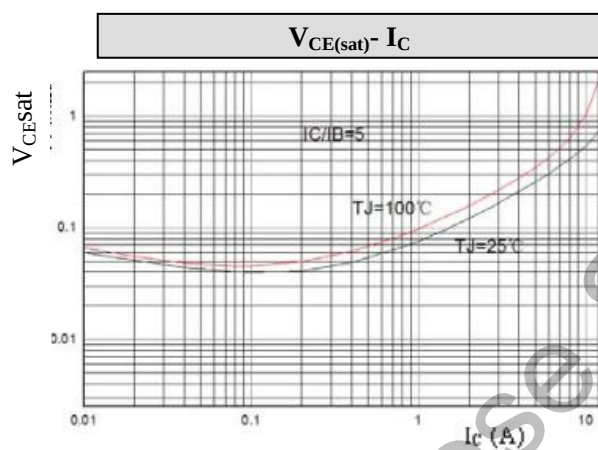
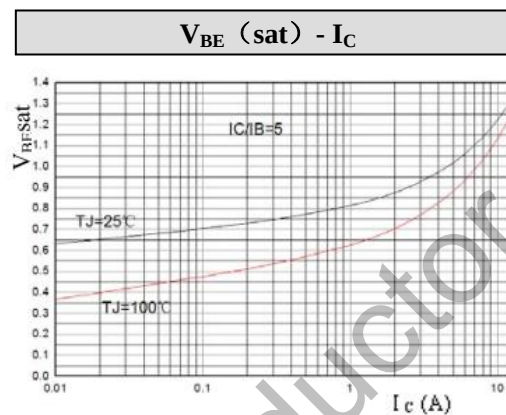
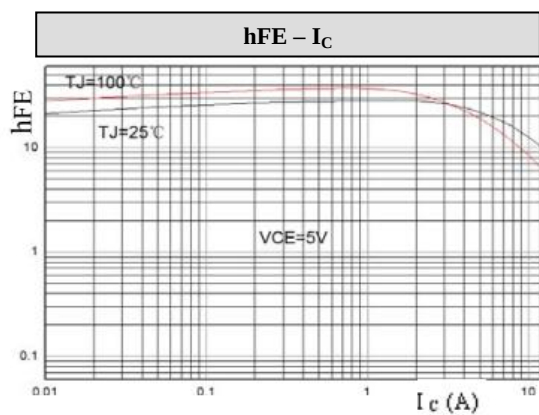
Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	700	V
V _{CEO}	Collector-Emitter Voltage	400	V
V _{EBO}	Emitter-Base Voltage	9	V
I _C	Collector Current (DC)	12	A
I _{CP}	Collector Current (Pulse)	24	A
I _B	Base Current	6	A
P _C	Collector Dissipation (T _C = 25°C)	100	W
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	-65 ~ 150	°C

Electrical CharacteristicsT_C = 25°C unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max	Units
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 10mA, I _B = 0	400			V
I _{EBO}	Emitter Cut-off Current	V _{EB} = 9V, I _C = 0			1	mA
h _{FE1} h _{FE2}	DC Current Gain *	V _{CE} = 5V, I _C = 2A V _{CE} = 5V, I _C = 5A	8 5		60 30	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 2A, I _B = 0.4A I _C = 5A, I _B = 1A I _C = 8A, I _B = 2A			1.0 2.0 3.0	V V V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 2A, I _B = 0.4A I _C = 5A, I _B = 1A			1.2 1.6	V V
f _T	Current Gain Bandwidth Product	V _{CE} = 10V, I _C = 0.5A	4			MHz
C _{ob}	Output Capacitance	V _{CB} = 10V, f = 0.1MHz		110		pF
t _{ON}	Turn On Time	V _{CC} = 125V, I _C = 5A			1.6	μs
t _{STG}	Storage Time	I _{B1} = -I _{B2} = 1A R _L = 25Ω			3.0	μs
t _F	Fall Time				0.7	μs

* Pulse Test: PW ≤ 300μs, Duty Cycle ≤ 2%

Typical Characteristics



Package Dimension

TO-3P

Unit: mm

